## Very Low I<sub>q</sub> LD0 150 mA Regulator with RESET and Delay Time Select

The NCV8660 is a precision very low Iq low dropout voltage regulator. Quiescent currents as low as  $28 \,\mu\text{A}$  typical make it ideal for automotive applications requiring low quiescent current with or without a load. Integrated control features such as Reset and Delay Time Select make it ideal for powering microprocessors.

It is available with a fixed output voltage of 5.0 V and 3.3 V and regulates within  $\pm 2.0\%$ .

#### Features

- Fixed Output Voltage of 5 V and 3.3 V
- $\pm 2.0\%$  Output Voltage up to V<sub>BAT</sub> = 40 V
- Output Current up to 150 mA
- Microprocessor Compatible Control Functions:
  - Delay Time Select
  - RESET Output
- NCV Prefix for Automotive
  - Site and Change Control
  - AEC-Q100 Qualified
- Low Dropout Voltage
- Low Quiescent Current of 28 μA Typical
- Stable Under No Load Conditions
- Protection Features:
  - Thermal Shutdown
  - Short Circuit
- These are Pb–Free Devices

#### Applications

- Automotive:
  - Body Control Module
  - Instrument and Clusters
  - Occupant Protection and Comfort
  - Powertrain
- Battery Powered Consumer Electronics



Figure 1. Application Diagram



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#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the dimensions section on page 12 of this data sheet.

#### **PIN DESCRIPTIONS**

Р	Pin		
DPAK	SOIC-8 FUSED	Symbol	Function
1	1	IN	Input Supply Voltage. 0.1 $\mu\text{F}$ bypass capacitor to GND at the IC.
2	2	R <sub>O</sub>	Reset Output. CMOS compatible output. Goes low when $V_{\text{OUT}}$ drops by more than 7% from nominal.
3, Tab	5–8	GND	Ground
4	3	DT	Reset Delay Time Select. Short to GND or connect to OUT to select time.
5	4	OUT	Regulated Voltage Output. 2.2 $\mu$ F to ground for typical applications.



Figure 2. Block Diagram

#### **ABSOLUTE MAXIMUM RATINGS**

Rating		Symbol	Min	Max	Unit
Input Voltage (IN)		V <sub>IN</sub>	-0.3	40	V
Input Current	I <sub>IN</sub>	-1.0	-	mA	
Output Voltage (OUT) DC Transient, t < 10 s (Note 1)	V <sub>OUT</sub>	-0.3 -0.3	5.5 16	V	
Output Current (OUT)		I <sub>OUT</sub>	-1.0	Current Limited	mA
Storage Temperature Range		T <sub>STG</sub>	-55	150	°C
DT (Reset Delay Time Select) Voltage (Note 2)		V <sub>DT</sub>	-0.3	16	V
DT (Reset Delay Time Select) Current (Note 2)		I <sub>DT</sub>	-1.0	1.0	mA
RO (Reset Output) Voltage DC Transient, t < 10 s		V <sub>RO</sub>	-0.3 -0.3	5.5 16	V
RO (Reset Output) Current		I <sub>RO</sub>	-1.0	1.0	mA
ESD CAPABILITY					
ESD Capability, Human Body Model (Note 3)		ESD <sub>HB</sub>	-2.0	2.0	kV
ESD Capability, Machine Model (Note 3)		ESD <sub>MM</sub>	-200	200	V
ESD Capability, Charged Device Model (Note 3)		ESD <sub>CDM</sub>	-1.0	1.0	kV
THERMAL RESISTANCE					
Junction-to-Case (Note 4)	DPAK 5	$R_{\theta JC}$	15		°C/W
Junction-to-Ambient (Note 4)	DPAK 5	$R_{\thetaJA}$	66		°C/W
Junction-to-Tab (Note 4)	DPAK 5	$R_{ extsf{ heta}JT}$	4.0		°C/W
Junction-to-Ambient (Note 4)	SOIC-8 FUSED	$R_{\theta JA}$	104		°C/W
Junction-to-Lead (pin 6) (Note 4)	SOIC-8 FUSED	$R_{\theta JT}$	33		°C/W
LEAD SOLDERING TEMPERATURE AND MSL					
Moisture Sensitivity Level	sture Sensitivity Level DPAK 5 SOIC-8 FUSED		1 3		_
Lead Temperature Soldering: SMD style only, Reflow (I Pb-Free Part 60 – 150 sec above 217°C, 40 sec max a		SLD	_	265 peak	°C

Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The output voltage must not exceed the input voltage.

The output voltage must not exceed the input voltage.
External resistor required to minimize current to less than 1 mA when the control voltage is above 16 V.
This device series incorporates ESD protection and is tested by the following methods: ESD HBM tested per AEC-Q100-002 (EIA/JESD22-A114) ESD MM tested per AEC-Q100-003 (EIA/JESD22-A115) ESD CDM tested per EIA/JESD22/C101, Field Induced Charge Model

Values represented typical steady-state thermal performance on 1 oz. copper FR4 PCB with 1 in<sup>2</sup> copper area.
Per IPC / JEDEC J-STD-020C.

#### **OPERATING RANGE**

Pin Symbol, Parameter	Symbol	Min	Max	Unit
V <sub>IN</sub> , Input Voltage Operating Range	V <sub>IN</sub>	4.5	40	V
Junction Temperature Range	TJ	-40	150	°C

### $\label{eq:expectation} \textbf{ELECTRICAL CHARACTERISTICS} \ 5.5 \ V < V_{IN} < 40 \ V, \ -40^{\circ}C \leq T_J \leq +150^{\circ}C, \ \text{unless otherwise specified}$

Characteristic	Symbol	Conditions	Min	Тур	Max	Unit
GENERAL						
Quiescent Current	۱ <sub>q</sub>	100 $\mu$ A < I <sub>OUT</sub> < 150mA, V <sub>IN</sub> = 13.2V, T <sub>J</sub> = 25°C	-	25	30	μΑ
		100 $\mu$ A < I <sub>OUT</sub> < 150mA, V <sub>IN</sub> = 13.2V, T <sub>J</sub> $\leq$ 85°C	-	-	40	
Thermal Shutdown (Note 6)	T <sub>SD</sub>		150	175	195	°C
Thermal Hysteresis (Note 6)	T <sub>HYS</sub>		-	25	-	°C

#### OUT

Output Voltage	V <sub>OUT</sub>	6 V $\leq$ V $_{IN}$ $\leq$ 16 V, 0.1 mA $\leq$ $I_{OUT}$ $\leq$ 150 mA	4.9	5.0	5.1	V
		6 V $\leq$ V <sub>IN</sub> $\leq$ 40 V, 0.1 mA $\leq$ I <sub>OUT</sub> $\leq$ 100 mA	4.9	5.0	5.1	
		5.6 V $\leq$ V $_{IN}$ $\leq$ 16 V, 0 mA $\leq$ I $_{OUT}$ $\leq$ 150 mA, $-40^\circ C \leq$ T $_J$ $\leq$ +125 $^\circ C$	4.9	5.0	5.1	
Output Voltage	V <sub>OUT</sub>	5.5 V $\leq$ V $_{IN}$ $\leq$ 16 V, 0.1 mA $\leq$ $I_{OUT}$ $\leq$ 150 mA	3.234	3.3	3.366	V
		$5.5 \text{ V} \le \text{V}_{\text{IN}} \le 40 \text{ V}, 0.1 \text{ mA} \le \text{I}_{\text{OUT}} \le 100 \text{ mA}$	3.234	3.3	3.366	
Output Current Limit	I <sub>CL</sub>	OUT = 96% x V <sub>OUT</sub> nominal	205	-	525	mA
Output Current Limit, Short Circuit	I <sub>SCKT</sub>	OUT = 0 V	205	-	525	mA
Load Regulation	$\Delta V_{OUT}$	$V_{IN} = 13.2 \text{ V}, I_{OUT} = 0.1 \text{ mA to } 150 \text{ mA}$	-40	10	40	mV
Line Regulation	$\Delta V_{OUT}$	$I_{OUT} = 5 \text{ mA}, V_{IN} = 6 \text{ V to } 28 \text{ V}$	-20	0	20	mV
Dropout Voltage – 5.0 V Only	V <sub>DR</sub>	$I_{OUT}$ = 100 mA, (Note 7) $V_{DR}$ = $V_{IN}-V_{OUT},~(\Delta V_{OUT}$ = –100 mV)	-	0.225	0.45	V
		$ \begin{array}{l} I_{OUT} = 150 \text{ mA, (Note 7)} \\ V_{DR} = V_{IN} - V_{OUT}, \ (\Delta V_{OUT} = -100 \text{ mV}) \end{array} $	-	0.30	0.60	
Output Load Capacitance	CO	Output capacitance for stability	2.2	-	-	μF
Power Supply Ripple Rejection	PSRR	V <sub>IN</sub> = 13.2 V, 0.5 V <sub>PP</sub> , 100 Hz	-	60	-	dB

#### DT (Reset Delay Time Select)

Threshold Voltage High		2	-	-	V
Low		-	-	0.8	V
Input Current	DT = 5 V	-	-	1.0	μΑ

#### RO, Reset Output

RESET Threshold	V <sub>Rf</sub>	V <sub>OUT</sub> decreasing		93	96	%V <sub>OUT</sub>
RESET Threshold Hysteresis	V <sub>Rhys</sub>			2.0	-	%V <sub>OUT</sub>
RO Output Low	V <sub>RL</sub>	10 k $\Omega$ RESET to OUT, V <sub>OUT</sub> = 4.5 V	-	0.2	0.4	V
RO Output High (OUT–RO) V <sub>RH</sub> 10		10 kΩ RESET to GND	V <sub>OUT</sub> -0.4	V <sub>OUT</sub> -0.2	V <sub>OUT</sub>	V
Reset Reaction Time	t <sub>RR</sub>	V <sub>OUT</sub> into UV to RESET Low	16	25	38	μsec
Input Voltage Reset Threshold VIN_RT		V <sub>IN</sub> Decreasing, V <sub>OUT</sub> > V <sub>RT</sub>	-	3.8	4.25	V

#### **RESET Delay with DT Selection**

Not production tested, guaranteed by design.
Dropout at a given current level is defined as the voltage difference of V<sub>IN</sub> to V<sub>OUT</sub> with V<sub>IN</sub> decreasing until the output drops by 100 mV.

#### **TYPICAL OPERATING CHARACTERISTICS**



#### **TYPICAL OPERATING CHARACTERISTICS**





Figure 13. Quiescent Current vs. Temperature

Figure 12. Quiescent Current vs. Input Voltage

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#### **TYPICAL OPERATING CHARACTERISTICS**



#### **TYPICAL OPERATING CHARACTERISTICS**





#### DETAILED OPERATING DESCRIPTION

#### General

The NCV8660 is a 5 V and 3.3 V linear regulator providing low drop-out voltage for 150 mA at low quiescent current levels. Also featured in this part is a reset output with selectable delay times. Delay times are selectable via part selection and control through the Delay Time Select (DT) pin. No pull-up resistor is needed on the reset output (RO). Pull-up and pull-down capability are included. Only a small bypass capacitor on the input (IN) supply pin and output (OUT) voltage pin are required for normal operation. Thermal shutdown functionality protects the IC from damage caused from excessively high temperatures appearing on the IC.

#### **Output Voltage**

Output stability is determined by the capacitor selected from OUT to GND. The NCV8660 has been designed to work with low ESR (equivalent series resistance) ceramic capacitors. The device is extremely stable using virtually any capacitor 2.2  $\mu$ F and above. Reference the Output Capacitor Stability graph in Figure 21.

The output capacitor value will affect overshoot during power-up. A lower value capacitor will cause higher overshoot on the output. System evaluation should be performed with minimum loading for evaluation of overshoot.

Selection of process technology for the NCV8660 allows for low quiescent current independent of loading. Quiescent current will remain flat across the entire range of loads providing a low quiescent current condition in standby and under heavy loads. This is highly beneficial to systems requiring microprocessor interrupts during standby mode as duty cycle and load changes have no impact on the standby current. Reference Figure 14 for Quiescent Current vs Output Current.

#### **Current Limit**

Current limit is provided on OUT to protect the IC. The minimum specification is 205 mA. Current limit is specified under two conditions (OUT = 96% x OUT nominal) and (OUT = 0 V). No fold-back circuitry exists. Any measured differences can be attributed to change in die temperature. The part may be operated up to 205 mA provided thermal die temperature is considered and is kept below 150°C. Degradation of electrical parameters at this current is expected at these elevated levels. A reset (RO) will not occur with a load less than 205 mA.

#### Reset Output

A reset signal is provided on the Reset Output (RO) pin to provide feedback to the microprocessor of an out of regulation condition. This is in the form of a logic signal on RO. Output (OUT) voltage conditions below the RESET threshold cause RO to go low. The RO integrity is maintained down to OUT = 1.0 V.

The Reset Output (RO) circuitry includes an active internal pullup to the output (OUT) as shown in Figure 24. No external pullup is neccessary.



Figure 24. Reset Output Circuitry



During power-up (or restoring OUT voltage from a reset event), the OUT voltage must be maintained above the Reset threshold for the Reset Delay time before RO goes high. The time for Reset Delay is determined by the choice of IC and the state of the DT pin.

#### **Reset Delay Time Select**

Selection of the NCV8660 device and the state of the DT pin determines the available Reset Delay times. The part is designed for use with DT tied to ground or OUT, but may be controlled by any logic signal which provides a threshold between 0.8 V and 2 V. The default condition for an open DT pin is the slower Reset time (DT = GND condition). Times are in pairs and are highlighted in the chart below. Consult factory for availability.

	DT=GND	DT=OUT
	Reset Time	Reset Time
NCV86601	8 ms	128 ms
NCV86602	8 ms	32 ms
NCV86603	16 ms	64 ms
NCV86604	32 ms	128 ms

The Delay Time select (DT) pin is logic level controlled and provides Reset Delay time per the chart. Note the DT pin is sampled only when RO is low, and changes to the DT pin when RO is high will not effect the reset delay time.

#### **Thermal Shutdown**

When the die temperature exceeds the Thermal Shutdown threshold, a Thermal Shutdown event is detected OUT is turned off, and RO goes low. The IC will remain in this state until the die temperature moves below the shutdown threshold (175°C typical) minus the hysteresis factor (25°C typical). The output will then turn back on and RO will go high after the RESET Delay time.





#### **ORDERING INFORMATION**

Device	Output Voltage	Reset Delay Time, DT to GND	Reset Delay Time, DT to OUT	Package	Shipping <sup>†</sup>
NCV86601DT50RKG		8 ms	128 ms		
NCV86602DT50RKG		8 ms	32 ms	DPAK	0500 (Taka 8 Daal
NCV86603DT50RKG		16 ms	64 ms	(Pb-Free)	2500 / Tape & Reel
NCV86604DT50RKG		32 ms	128 ms		
NCV86601D50G	5.0 V	8 ms	128 ms		98 Units / Rail
NCV86601D50R2G		8 ms	128 ms		
NCV86602D50R2G		8 ms	32 ms	SOIC-8 FUSED (Pb-Free)	
NCV86603D50R2G		16 ms	64 ms		2500 / Tape & Reel
NCV86604D50R2G		32 ms	128 ms		
NCV86601DT33RKG		8 ms	128 ms		
NCV86602DT33RKG		8 ms	32 ms	DPAK	
NCV86603DT33RKG		16 ms	64 ms	(Pb-Free)	2500 / Tape & Reel
NCV86604DT33RKG		32 ms	128 ms		
NCV86601D33R2G	3.3 V	8 ms	128 ms		
NCV86602D33R2G	1	8 ms	32 ms	SOIC-8 FUSED	
NCV86603D33R2G	1	16 ms	64 ms	(Pb-Free)	2500 / Tape & Reel
NCV86604D33R2G	1	32 ms	128 ms		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.





**DPAK-5, CENTER LEAD CROP** CASE 175AA **ISSUE B** 

DATE 15 MAY 2014

SCALE 1:1



#### RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIM	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.235	0.245	5.97	6.22	
в	0.250	0.265	6.35	6.73	
С	0.086	0.094	2.19	2.38	
D	0.020	0.028	0.51	0.71	
Е	0.018	0.023	0.46	0.58	
F	0.024	0.032	0.61	0.81	
G	0.180	BSC	4.56	BSC	
н	0.034	0.040	0.87	1.01	
J	0.018	0.023	0.46	0.58	
К	0.102	0.114	2.60	2.89	
L	0.045	BSC	1.14 BSC		
R	0.170	0.190	4.32	4.83	
<b>R</b> 1	0.185	0.210	4.70	5.33	
S	0.025	0.040	0.63	1.01	
U	0.020		0.51		
v	0.035	0.050	0.89	1.27	
Z	0.155	0.170	3.93	4.32	

#### GENERIC **MARKING DIAGRAMS\***



\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " .", may or may not be present.

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#### SOIC-8 NB CASE 751-07 **ISSUE AK**

STYLE 1: PIN 1. EMITTER COLLECTOR 2. 3. COLLECTOR 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT IOUT 6. IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4 SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5.

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8 GATE 1

SOURCE 1/DRAIN 2

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. З. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 MIRROR 1 8. STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT OVI O 2 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

#### DATE 16 FEB 2011

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 З. BASE #2 COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6 DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW\_TO\_GND 2. DASIC OFF DASIC\_SW\_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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